







# METHOD OF FORMING METALLIC AND CERAMIC THIN FILM STRUCTURES USING METAL HALIDES AND ALKALI METALS

**Patent number:** WO9844164  
**Publication date:** 1998-10-08  
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**Classification:**  
**- international:** C23C16/14; C23C16/34; C23C16/44; C23C16/06; C23C16/34; C23C16/44; (IPC1-7): C23C16/06; C23C16/22; C23C16/30  
**- european:** C23C16/14; C23C16/34  
**Application number:** WO1998US06644 19980403  
**Priority number(s):** US19970041965P 19970403; US19970061443P 19971009

Also published as:

 WO9844164 (A1)

Cited documents:

 US3244482  
 US5021221  
 US5453124  
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 US5498446

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## Abstract of WO9844164

A new low temperature method for nanostructured metal and ceramic thin film growth by chemical vapor deposition (CVD) involves the use of a low pressure co-flow diffusion flame reactor to react alkali metal vapor and metal halide vapor to deposit metal, alloy and ceramic films. The reaction chemistry is described by the following general equation:  $(mn)Na + nMX_m \rightarrow (M)n + (nm)NaX$  where Na is sodium, or another alkali metal (e.g., K, Rb, Cs), and  $MX_m$  is a metal-halide (M is a metal or other element such as Si, B or C; X is a halogen atom, e.g., chlorine, fluorine or the like; and m and n are integers). This reaction chemistry is a viable technique for thin film growth. In one mode, using the precursors of sodium metal vapor, titanium tetrachloride (the limiting reagent), and either argon or nitrogen gases, titanium (Ti), titanium nitride (TiN), titanium dioxide (TiO<sub>2</sub>), and titanium silicide (TiSi, Ti<sub>5</sub>Si<sub>3</sub>, TiSi<sub>2</sub>, Ti<sub>5</sub>Si<sub>4</sub>) thin films have been successfully grown on copper and silicon substrates. Conditions can be adjusted to prevent or minimize gas-phase particle nucleation and growth. Substrate temperatures can also be varied to prevent excessive salt deposition.

POTENTIAL FILMS WHICH CAN BE GROWN WITH THE SODIUM/METAL HALIDE CVD REACTOR VS. CONVENTIONAL CVD

| Potential film structure | conventional CVD temperature | new method | conventional CVD growth rate for the metal halide in nitrogen (g) |
|--------------------------|------------------------------|------------|---|
| Si                       | 900-1100°C                   | 450°C      | 100%  |
| TiN                      | 900-1100°C                   | 450°C      | 100%, or 100%   |
| Si                       | 900-1100°C                   | 450°C      | 100%, or 100%   |
| Ti                       | 900-1100°C                   | 450°C      | 100%  |
| TiN                      | 900-1100°C                   | 450°C      | 100%, or 100%   |
| Si                       | >1100°C                      | 450°C      | 100%, or 100%, or 100%  |

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